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BLM7G22S-60PBG

W-CDMA 2110 MHz to 2170 MHz 2-stage power MMC

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Quick ordering

BLM7G22S-60PBG,118

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The BLM7G22S-60PB(G) is a dual path 2-stage power MMC using NXP's state of the art GEN7 LDMOS technology. This device is perfectly suited as general purpose driver in the frequency range from 2100 MHz to 2200 MHz. Available in gull wing or flat lead outline.

Features and benefits

- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated current sense
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use
- Designed for broadband operation (2100 MHz to 2200 MHz)
- Compliant to Directive 2002/95/EC, regarding RoHS

Applications

- W-CDMA base stations in the 2100 to 2200 frequency range

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Parametrics of this product

Symbol	Parameter	Conditions	Min	Typ/Nom	Max	Unit
f_{range}	frequency range		2100		2200	MHz
$P_{L(1dB)}$	nominal output power at 1 dB gain compression			60		W
Test signal: 2-c WCDMA						
G_p	power gain	$V_{DS} = 28 \text{ V}; P_{L(AV)} = 1.6 \text{ W}$		29.9		dB
RL_{in}	input return loss	$V_{DS} = 28 \text{ V}; I_{DQ} = 233 \text{ mA}; P_{L(AV)} = 1.6 \text{ W}$		-12		dB
η_D	drain efficiency	$V_{DS} = 28 \text{ V}; f = 2140 \text{ Hz}; I_{DQ} = 233 \text{ mA}; P_{L(AV)} = 1.6 \text{ W}$		11.5		%
ACPR	adjacent channel power ratio	$P_{L(AV)} = 1.6 \text{ W}; V_{DS} = 28 \text{ V}; I_{DQ} = 233 \text{ mA}; f = 2140 \text{ Hz}$		-43		dBc

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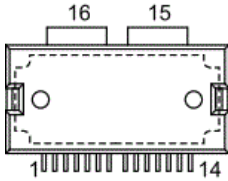
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Package

Type number	Orderable part number	Ordering code (12NC)	Product status	Package	Packing	Marking
BLM7G22S-60PBG	BLM7G22S-60PBG,118	9340 660 83118	Volume production	SOT1212-1 (HSOP16)	Reel Pack, SMD, 13"	Standard Marking

Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	V _{DS} (A1)	drain-source voltage of stage A1		
2	V _{GSS} (A2)	gate sense FET and gate source voltage of stage A2		
3	V _{DSS} (A2)	drain sense FET source voltage of stage A2		
4	RF_IN_A	RF input path A		
5	V _{GSS} (A1)	gate sense FET and gate source voltage of stage A1		
6	V _{DSS} (A1)	drain sense FET source voltage of stage A1		
7	n.c.	not connected		
8	n.c.	not connected		
9	V _{DSS} (B1)	drain sense FET source voltage of stage B1		
10	V _{GSS} (B1)	gate sense FET and gate source voltage of stage B1		
11	RF_IN_B	RF input path of B		
12	V _{DSS} (B2)	drain sense FET source voltage of stage B2		
13	V _{GSS} (B2)	gate sense FET and gate source voltage of stage B2		
14	V _{DS} (B1)	drain-source voltage of stage B1		
15	RF_OUT_A/V _{DS} (A2)	RF output path A / drain source voltage of stage A2		
16	RF_OUT_B/V _{DS} (B2)	RF output path B / drain source voltage of stage B2		
17	GND	RF ground		

Outline drawing

Package Version	Package Name	Package Description	Reference Codes	Issue Date
 SOT1212-1	HSOP16	plastic, heatsink small outline package; 16 leads(flat)		2012-03-30

Quality, reliability & chemical content

Type number	Orderable part number	Chemical content	RoHS	Leadfree conversion date	RHF	IFR (FT)	MTBF (hours)	MSL	MSL LF
BLM7G22S-60PBG	BLM7G22S-60PBG,118	BLM7G22S-60PBG						3	3

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Documentation for this product

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File name	Title	Type	Format	Date
 AN10896	Mounting and Soldering of RF transistors	Application note	pdf	2010-06-02
 75017119	Your partner in Mobile Communication Infrastructure design; High Performance RF for wireless infrastructure	Brochure	pdf	2011-05-23
 fatigue_in_aluminum_bond_wires	Fatigue in aluminum bond wires	Mounting and soldering	pdf	2009-10-08
 75017272	NXP's RF Manual 16th edition	Selection guide	pdf	2012-06-08

Ordering & availability

Type number	Ordering code (12NC)	Orderable part number	Region	Distributor	In stock	Order quantity	Inventory date	Buy online	Samples
BLM7G22S-60PBG	9340 660 83118	BLM7G22S-60PBG,118							Order samples

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